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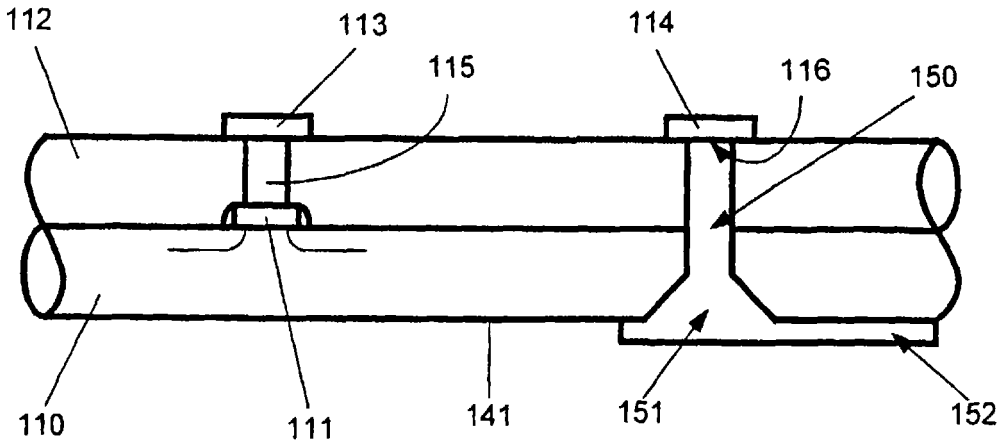
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(54) Title: BACKSIDE CONTACT FOR INTEGRATED CIRCUIT AND METHOD OF FORMING SAME



(57) Abstract: A contact (146) formed from the backside of an integrated circuit device includes a first conductive layer (114) on a first surface of the integrated circuit device and a second conductive layer on a second surface (141) of the device. The two conductive layers are coupled by way of an opening (144) through the semiconductor substrate (110) separating the two conductive layers. A method for making the backside contact (146) comprises forming the first conductive layer (114), forming an opening (144) through the semiconductor substrate (110) to expose at least a portion of the underside (116) of the first conductive layer (114), then filling the opening (144) with a conductive material (150) to provide an electrical contact to the first conductive layer (114) from the backside of the integrated circuit device.

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